ABSTRACT

A method of performing immersion lithography on a semiconductor wafer is provided. The method includes providing a layer of resist onto a surface of the semiconductor wafer. Next, an edge-bead removal process spins the wafer at a speed greater than 1000 revolutions per minute and dispenses solvent through a nozzle while the wafer is spinning. Then, the resist layer is exposed using an immersion lithography exposure system.

FIGURE 3